# **Quad 3-State Noninverting Buffers**

# **High-Performance Silicon-Gate CMOS**

The MC74HC125A and MC74HC126A are identical in pinout to the LS125 and LS126. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC125A and HC126A noninverting buffers are designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low (HC125A) or active-high (HC126A).

### **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



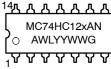
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# MARKING DIAGRAMS

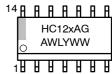


PDIP-14 N SUFFIX CASE 646





SOIC-14 D SUFFIX CASE 751A



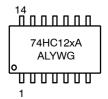


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 F SUFFIX CASE 965



x = 5, 6

A = Assembly Location

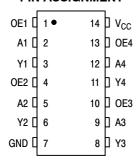
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# **PIN ASSIGNMENT**



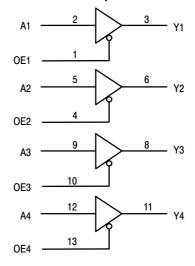
# **FUNCTION TABLE**

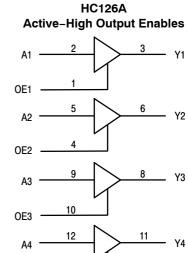
HC125A				
Inp	outs	Output		
Α	OE	Υ		
Н	L	Н		
L	L	L		
Х	Н	Z		

HC126A					
In	outs	Output			
Α	OE	Υ			
Н	Н	Н			
L	Н	L			
Χ	L	Z			

## **LOGIC DIAGRAM**

# HC125A Active-Low Output Enables





13

PIN 14 = V<sub>CC</sub> PIN 7 = GND

OE4

# **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-$ 0.5 to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	٧
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{\rm CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)			6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Types		<b>- 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	(Figure 1) V <sub>CC</sub>	; = 2.0 V ; = 4.5 V ; = 6.0 V	0	1000 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$	2.0	1.5	1.5	1.5	V
		$ I_{out}  \le 20 \mu\text{A}$	3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V	2.0	0.5	0.5	0.5	V
		$ I_{\text{out}}  \leq 20 \mu\text{A}$	3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output	$V_{in} = V_{IH}$	2.0	1.9	1.9	1.9	V
	Voltage	$ I_{out}  \leq 20 \mu\text{A}$	4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		$V_{in} = V_{IH}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	2.48	2.34	2.2	
		$ I_{\text{out}}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
		$ I_{\text{out}}  \leq 7.8 \text{ mA}$	6.0	5.48	5.34	5.2	
V <sub>OL</sub>	Maximum Low-Level Output	$V_{in} = V_{IL}$	2.0	0.1	0.1	0.1	V
	Voltage	I <sub>out</sub>   ≤ 20 μA	4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		$V_{in} = V_{IL}$ $ I_{out}  \le 3.6 \text{ mA}$	3.0	0.26	0.33	0.4	
		$ I_{\text{out}}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
		$ I_{\text{out}}  \leq 7.8 \text{ mA}$	6.0	0.26	0.33	0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>OZ</sub>	Maximum Three-State Leakage	Output in High-Impedance State	6.0	± 0.5	± 5.0	± 10	μΑ
	Current	$V_{in} = V_{IL}$ or $V_{IH}$					
		V <sub>out</sub> = V <sub>CC</sub> or GND					
Icc	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	4.0	40	160	μΑ
	(per Package)	I <sub>out</sub> = 0 μA					

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \ pF$ , Input $t_r = t_f = 6.0 \ ns$ )

			Guaranteed Limit			
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 3.0 4.5 6.0	90 36 18 15	115 45 23 20	135 60 27 23	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	120 45 24 20	150 60 30 26	180 80 36 31	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	90 36 18 15	115 45 23 20	135 60 27 23	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	рF
C <sub>out</sub>	Maximum 3-State Output Capacitance (Output in High-Impedance State)	-	15	15	15	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Per Buffer)*		Typical	@ <b>25°C</b> , V <sub>C</sub>	<sub>C</sub> = 5.0 V	pF

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC125ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HC125ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC125ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HC125ADTG	TSSOP-14*	96 Units / Rail
MC74HC125ADTR2G	TSSOP-14*	2500 / Tape & Reel
MC74HC125AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HC125AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel
MC74HC126ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HC126ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC126ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HC126ADTR2G	TSSOP-14*	2500 / Tape & Reel
MC74HC126AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb-Free.

# **SWITCHING WAVEFORMS**

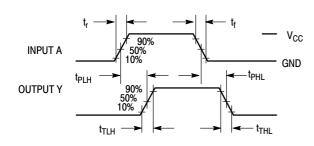


Figure 1.

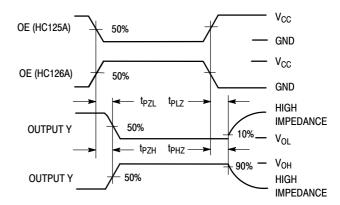
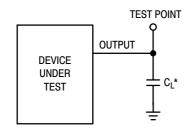


Figure 2.



\*Includes all probe and jig capacitance

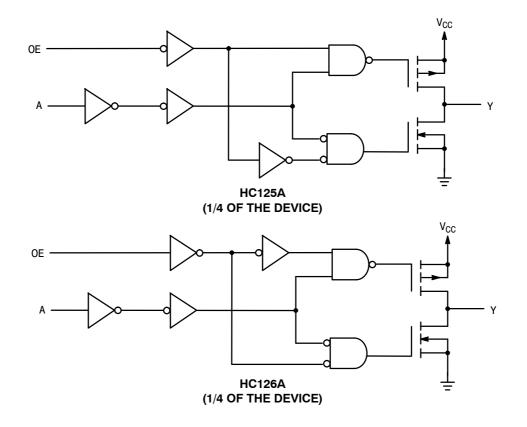
DEVICE UNDER TEST  $C_L^*$ TEST POINT

CONNECT TO  $V_{CC}$  WHEN TESTING  $t_{PLZ}$  AND  $t_{PZL}$ . CONNECT TO GND WHEN TESTING  $t_{PHZ}$  and  $t_{PZH}$ .

\*Includes all probe and jig capacitance

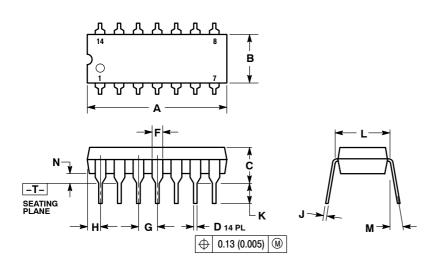
Figure 3. Test Circuit

Figure 4. Test Circuit



# **PACKAGE DIMENSIONS**

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE P

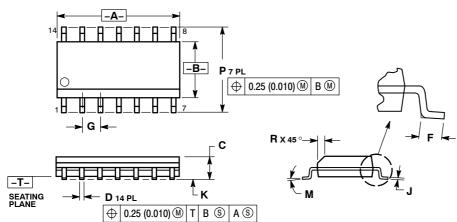


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M		10 °		10 °
N	0.015	0.039	0.38	1.01

# PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J** 

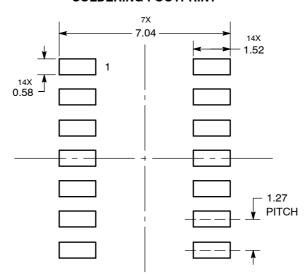


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

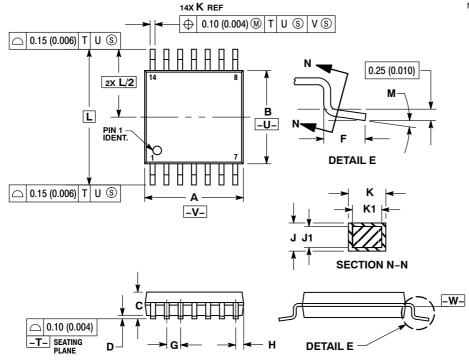
	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# **SOLDERING FOOTPRINT**



## PACKAGE DIMENSIONS

# TSSOP-14 **DT SUFFIX** CASE 948G-01 ISSUE B



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

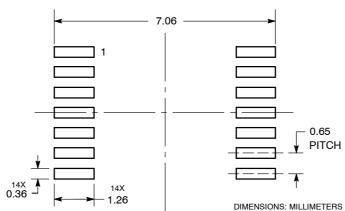
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  - DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  - INTERLEAD FLASH OR PROTRUSION.
    INTERLEAD FLASH OR PROTRUSION SHALL
    NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08
    (0.003) TOTAL IN EXCESS OF THE K
    DIMENSION AT MAXIMUM MATERIAL
    CONDITION.
    6. TERMINAL NUMBERS ARE SHOWN FOR
    REFERENCE ONLY

  - REFERENCE ONLY.

    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

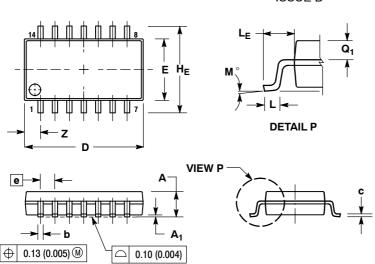
	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	0 °	8 °	0 °	8 °

## **SOLDERING FOOTPRINT**



#### PACKAGE DIMENSIONS

# SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE B**



#### NOTES:

- 1. DIMENO... Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE
- MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE, MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
М	0 °	10°	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

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